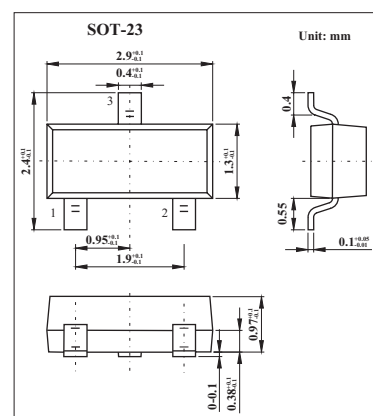


Silicon PIN Diode

BA886

■ Features

- Current-controlled RF resistor for switching and attenuating applications
- Frequency range above 1 M
- Designed for low IM distortion

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Value	Unit
Reverse Voltage	V_R	50	V
Forward Current	I_F	50	mA
Operating temperature range	T_{op}	-55 to +125	$^\circ\text{C}$
Storage temperature range	T_{stg}	-55 to +150	$^\circ\text{C}$
Junction ambient	R_{thJA}	≤ 450	K/W

Note:

1. Package mounted on alumina $15\text{ mm} \times 16.7\text{ mm} \times 0.7\text{ mm}$.

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit	
Forward Voltage	V_F	$I_F = 50\text{ mA}$			1.15	V	
Reverse Current	I_R	$V_R = 50\text{ V}$			50	nA	
Diode capacitance	C_T	$V_R = 50\text{ V}, f = 1\text{ MHz}$		0.23	0.35	pF	
		$V_R = 0\text{ V}, f = 100\text{ MHz}$		0.20			
Forward resistance	r_f	$f = 100\text{ MHz}$				Ω	
		$I_F = 10\ \mu\text{ A}$		2400			
		$I_F = 1\text{ mA}$			58		
		$I_F = 10\text{ mA}$	6.5	7.8	10		
Zero bias conductance	g_p	$V_R = 0\text{ V}, f = 100\text{ MHz}$		40		$\mu\text{ S}$	
Series inductance	L_s			2		nH	

■ Marking

Marking	PC
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